

# Peizhi Wang

## List of Publications by Year in descending order

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16  
papers

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134  
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#	ARTICLE	IF	CITATIONS
1	Crack damage control for diamond wire sawing of silicon: The selection of processing parameters. <i>Materials Science in Semiconductor Processing</i> , 2022, 148, 106838.	1.9	8
2	Fabrication of thin resin-bonded diamond wire and its application to ductile-mode wire sawing of mono-crystalline silicon. <i>Materials Science in Semiconductor Processing</i> , 2021, 126, 105665.	1.9	13
3	Study on Mechanisms of Photon-Induced Material Removal on Silicon at Atomic and Close-to-Atomic Scale. <i>Nanomanufacturing and Metrology</i> , 2021, 4, 216-225.	1.5	26
4	Effect of scratching speed on phase transformations in high-speed scratching of monocrystalline silicon. <i>Materials Science &amp; Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2020, 772, 138836.	2.6	14
5	Effect of speed on material removal behavior in scribing of monocrystalline silicon. <i>Precision Engineering</i> , 2020, 66, 315-323.	1.8	10
6	Modeling and simulation of phase transformation and crack formation during scribing of mono-crystalline silicon. <i>International Journal of Mechanical Sciences</i> , 2020, 175, 105527.	3.6	13
7	Interaction of lateral cracks in double scratching of single-crystal silicon carbide. <i>Theoretical and Applied Fracture Mechanics</i> , 2019, 104, 102378.	2.1	13
8	Material removal mechanism and crack propagation in single scratch and double scratch tests of single-crystal silicon carbide by abrasives on wire saw. <i>Ceramics International</i> , 2019, 45, 384-393.	2.3	41
9	Stress analysis in scratching of anisotropic single-crystal silicon carbide. <i>International Journal of Mechanical Sciences</i> , 2018, 141, 1-8.	3.6	28
10	Coupling stress caused by thermal and slicing force in KDP crystal slicing with fixed abrasive wire saw. <i>International Journal of Advanced Manufacturing Technology</i> , 2018, 96, 4333-4343.	1.5	17
11	The interaction of periodically distributed parallel cracks in anisotropic materials subjected to concentrated loads. <i>Engineering Fracture Mechanics</i> , 2018, 199, 131-142.	2.0	5
12	Prediction of sawing force for single-crystal silicon carbide with fixed abrasive diamond wire saw. <i>Materials Science in Semiconductor Processing</i> , 2017, 63, 25-32.	1.9	61
13	A scratching force model of diamond abrasive particles in wire sawing of single crystal SiC. <i>Materials Science in Semiconductor Processing</i> , 2017, 68, 21-29.	1.9	23
14	Effect of wire speed on subsurface cracks in wire sawing process of single crystal silicon carbide. <i>Engineering Fracture Mechanics</i> , 2017, 184, 273-285.	2.0	13
15	Fracture strength of silicon wafers sawn by fixed diamond wire saw. <i>Solar Energy</i> , 2017, 157, 427-433.	2.9	20
16	Prediction of the thickness for silicon wafers sawn by diamond wire saw. <i>Materials Science in Semiconductor Processing</i> , 2017, 71, 133-138.	1.9	11